WHAT IS CLAIMED IS:

1. A precision-of-register measuring mark, comprising:

a pair of register mark patterns spaced on a wafer; and

a resist pattern provided between the pair of register mark patterns and symmetrical in a direction of the arrangement of the pair of register mark patterns resulting from dual exposure.

2. A precision-of-register measuring mark according to Claim 1, wherein the resist pattern has a simple rectangular form.

3. A precision-of-register measuring method, comprising the steps of:

forming a resist film on a wafer having a pair of spaced mark patterns;

forming a first rendering pattern by rendering on the wafer a mask pattern symmetrical in the direction of the arrangement of the pair of mark patterns as a result of a first exposure in register with the register mark pattern;

forming a second rendering pattern by rendering on

the wafer the mask pattern as a result of a second exposure in register with the register mark pattern;

developing to form a resist pattern where the first rendering pattern and the second rendering pattern overlap; and

calculating the precision of register by (X1+X2)/2-(X3+X4)/2 where, in the register direction of the mask patterns, the coordinate of one side of one of the pair of register mark patterns is X1, the coordinate of one side of the other of the pair of register mark patterns and symmetrical to the one side of the one register mark pattern is X2, and the coordinates of two sides of the resist pattern are X3 and X4.

4. A precision-of-register measuring method according to Claim 3, wherein the mark pattern has a simple rectangular form.